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™FORMATION DISCLOSURE STATEMENT BY APPLICANT

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of 9

Sheet 1

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Application Number	10/625,480
Filing Date	July 22, 2003
First Named Inventor	Chen, et al.
Group Art Unit	2818
Examiner Name	Phuc T. Dang
Attorney Docket Number	AMAT/5335.Y1/CPI/COPPER/PJS
Submission Date	April 1, 2005

			U.S. PATENT	DOCUMENTS	
xaminer nitials*	Cite No.1 Document Number Number-Kind Code <sup>2</sup> (ff known)		Publication Date Name of Patentee or		Pages, Columns, Lines, Where Relevant Passages or Relevant
	+			P P	Figures Appear
P.D.	A1	US-4486487	12/4/1984	Suntola, et al. Skap	
<u> </u>	A2	US-5306666	4/26/1994	Izumi, et al.	
	·· A3	US-5374570	12/20/1994	Nasu, et al	
<i>3</i> ·	A4	US-5503875	4/2/1996	Imai, et al.	
	A5	US-5526244	6/11/1996	Bishop	
<u> </u>	A6	US-5711811 1751 15	1/27/1998	Suntola, et al.	·
	1 A7	*US=5916365 - * * * * * * * * * * * * * * * * * *	6/29/1999	Sherman · ·	
	A8	US-6015590	1/18/2000	Suntola, et al.	
	A9	US-6107208'	8/22/2000	Cheng, et al.	
	A10	'US-6139700 '	10/31/2000	Kang, et al.	
··· 17.47 =	'A11	'US-6174809''	1/16/2001	Kang, et al.	·
	A12	US-6197683	3/6/2001	Kang, et al.	
x369e27	Ã13	US-6200893	3/12/2001	Sneh	
uliala.	A14	US-6203613	3/20/2001	Gates, et al.	
	A15	US-6207302	3/27/2001	Sugiura, et al.	
	A16	US-6207487	3/27/2001	Kim, et al.	
	A17	US-6270572	8/7/2001	Kim, et al.	
	A18	US-6284646	9/4/2001	Leem	
	- A19	US-6287965	9/11/2001	Kang, et al.	
	. A20	US-6305314	10/23/2001	Sneh, et al.	
	A21	US-6342277	1/29/2002	Sherman	
	A22	US-6348376	2/19/2002	Lim, et al.	
	A23	US-6358829	3/19/2002	Yoon, et al.	
	A24	US-6372598	4/16/2002	Kang, et al.	
	/ A25	US-6391785	5/21/2002	Satta, et al.	
.	A26	US-6391803	5/21/2002	Kim, et al.	
/	A27	US-6399491	6/4/2002	Jeon, et al.	
PP	A28	US-6416577	7/9/2002	Suntoloa, et al.	

PHUC T. DANG **Date Considered** Examiner EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include

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Substitute for	form 1449A/PTO		Application Number	10/625,480
· · · · · · · · · · · · · · · · · · ·			Filing Date	July 22, 2003
INFORM	MATION DISCL	OSURE	First Named Inventor	Chen, et al.
STATE	MENT BY APP	LICANT	Group Art Unit	2818
· ·			Examiner Name	Phuc T. Dang
(Use as many sheets as necessary)			Attorney Docket Number	AMAT/5335.Y1/CPI/COPPER/PJS
Sheet 2		of 9	Submission Date	April 1, 2005

· · .			U.S. PATENT	DOCUMENTS		
Examiner Initials*			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
	A29	US-6416822	7/9/2002	Chiana at al	rigures Appear	
0.0	A30	US-6428859		Chiang, et al.		
-1		US-6451119 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	8/6/2002	Chiang, et al.		
	A31		9/17/2002	Sneh, et al.	•	
13:11	· A32	US-6451695-,	9/17/2002	Sneh		
	A33	US-6458701	10/1/2002	Chae, et al.		
	A34	US-6468924** \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	10/22/2002	Lee, et al.		
!	A35	US-6475276	11/5/2002	Elers, et al.		
	A36.	US-6475910	11/5/2002	Sneh	;	
	A37-	US-6478872 <sup>17</sup> - 7	11/12/2002	Chae, et al.		
	A38	US-6482733"	11/19/2002	Raaijmakers, et al.		
**************************************	A39	US-6495461 "	12/17/2002	Tsubouchi, et al.		
	A40	US-6511539	1/28/2003	Raaijmakers "		
	A41	US-6534395	3/18/2003	Werkhoven, et al.	<del></del>	
aistrit <b>s</b> "	A42	US-6548424	4/15/2003	Putkonen		
	A43	US-6551929	4/22/2003	Kori, et al.		
:	À44	US-6569501	5/27/2003	Chiang, et al.		
	A45	US-6596602	7/22/2003	lizuka, et al.		
	A46	US-6596643	7/22/2003	Chen, et al.		
	A47	US-6599572 "	7/29/2003	Saanila, et al.		
	A48	US-6607976	8/19/2003	Chen, et al.		
	A49	US-6620670	9/16/2003	Song, et al.		
; .	A50	US-6620723	9/16/2003	Byun, et al.		
	A51	US-6630201	10/7/2003	Chiang, et al.		
	A52	US-6630413	10/7/2003	Todd		
	A53	US-6632279	10/14/2003	Ritala, et al.		
···//	A54	US-6660660	12/9/2003	Haukka, et al.	<u> </u>	
\/	A55	US-6686271	2/3/2004	Raaijmakers, et al.		
, P.D	A56	US-6803272	10/12/2004	Halliyal, et al.		

Examiner PHUCT DANG Date Considered 5/17/2005

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Substitute	for form 1449A/PTO			Application Number	10/625,480
		•		Filing Date	July 22, 2003
INFO	RMATION DISC	LOS	SURE	First Named Inventor	Chen, et al.
STAT	STATEMENT BY APPLICANT			Group Art Unit	2818
				Examiner Name	Phuc T. Dang
(Use as many sheets as necessary)				Attorney Docket Number	AMAT/5335.Y1/CPI/COPPER/PJS
Sheet	3	of	9	Submission Date	April 1, 2005

			U.S. PATENT	DOCUMENTS	
Examiner	Cite	Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where
nitials*	Number-Kind Code <sup>2 (il known)</sup>		MM-DD-YYYY	Applicant of Cited Document	Relevant Passages or Relevant Figures Appear
PP.	A57	US-20010000866	5/10/2001	Sneh, et al.	
<u> </u>	A58	US-20010002280	5/31/2001	Sneh	
, , - m	A59	US-20010009140	7/26/2001	Bondestam, et al.	
	A60	US-20010009695	7/26/2001	Saanila, et al.	<del></del>
	A61	US-20010024387	9/27/2001	Raaijmakers, et al.	
	A62	US-20010024871	9/27/2001	Yagi	
	A63	US-20010028924	10/11/2001	Sherman	
	A64	US-20010034123	10/25/2001	Jeon, et al.	
	A65	US-20010041250	11/15/2001	Werkhoven, et al.	
77.	. A66	US-20010050039	12/13/2001	Park, et al.	
<u> </u>	'A67	US-20010054730	12/27/2001	Kim, et al.	
	A68	US-20020000598	1/3/2002	Kang, et al.	
Sparat	A69	US-20020007790	1/24/2002	Park	
ediae t	A70	US-20020016084	2/7/2002	Todd	<del></del>
	A71	US-20020021544	2/21/2002	Cho, et al.	·
	A72	US-20020031618	3/14/2002	Sherman	<del></del> ,
	A73	US-20020041931	4/11/2002	Suntola, et al.	,
	A74	US-20020047151	4/25/2002	Kim, et al.	
·· ·	A75	US-20020048635	4/25/2002	Kim, et al.	
,-	A76	US-20020052097	5/2/2002	Park	
	A77	US-20020060363	5/23/2002	Xi, et al.	
	A78	US-20020068458	6/6/2002	Chiang, et al.	
	A79	US-20020073924	6/20/2002	Chiang, et al.	
4	A80	US-20020074588	6/20/2002	Lee	
·	A81	US-20020076481	6/20/2002	Chiang, et al.	
17	A82	US-20020076507	6/20/2002	Chiang, et al.	
/	A83	US-20020076508	6/20/2002	Chiang, et al.	
PD	A84	US-20020081844	6/27/2002	Jeon, et al.	

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Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number. 10/625,480 Substitute for form 1449A/PTO Application Number Filing Date July 22, 2003 INFORMATION DISCLOSURE First Named Inventor Chen, et al. STATEMENT BY APPLICANT 2818 Group Art Unit Phuc T. Dang Examiner Name (Use as many sheets as necessary) AMAT/5335.Y1/CPI/COPPER/PJS Attorney Docket Number 9 Sheet of **Submission Date** April 1, 2005

1			U.S. PATENT	DOCUMENTS		
Examiner	Cite	Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where	
nitiais"	itials* No.¹ Number-Kind Code² (if known)		MM-DD-YYYY	Applicant of Cited Document	Relevant Passages or Relevant Figures Appear	
PD	A		7/4/2002	Byun, et al.	<del></del>	
$\overline{\Lambda}$	A86	US-20020086507	7/4/2002	Park, et al.		
	-A87	US-20020094689	7/11/2002	Sandhu, et al.		
	A88	US-20020104481	7/18/2002	Bachhofer, et al.	·	
	A89	US-20020106536	8/8/2002	Lee, et al.		
	A90	US-20020117399	8/29/2002	Chen, et al.		
	A91	US-2002013507.1	9/26/2002	-Kang, et al.		
	A92	US-20020144655	10/10/2002	Chiang, et al		
	A93	US-20020144657	10/10/2002	Chiang, et al.	<u> </u>	
	A94	US-20020146511	10/10/2002	Chiang, et al.		
×1,000	- A95	US-20020155722	10/24/2002	Satta, et al.		
	A96	US-20020162506	11/7/2002	Sneh, et al.		
tras r	A97	US-20020164421	11/7/2002	Chiang, et al.		
1,0,5 (10.0)	A98	US-20020164423	11/7/2002	Chiang, et al.		
	A99	US-20020172768	11/21/2002	Endo, et al.		
	A100	US-20020177282	11/28/2002	Song		
	A101	US-20020182320	12/12/2002	Leskela, et al.	<del></del>	
	A102	US-20020187256	12/12/2002	Elers, et al.	,	
	A103	US-20020187631	12/12/2002	Kim, et al.	,	
	A104	US-20020197402	12/26/2002	Chiang, et al.		
	A105 .	US-20020197863	12/26/2002	Mak, et al.		
	A106	US-20030013300	1/16/2003	Byun		
	A107	US-20030013320	1/16/2003	Kim, et al.		
• • •	A108	US-20030031807	2/13/2003	Elers, et al.		
	A109	US-20030032281	2/13/2003	Werkhoven, et al.		
1/	A110	US-20030042630	3/6/2003	Babcoke, et al.		
· · <b>\</b>	A111	US-20030049931	3/13/2003	Byun, et al.		
PD	A112	US-20030049942	3/13/2003	Haukka, et al.		

PHUC T. DANG **Date Considered** 17/2005 Examiner

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Substitute	for form 1449A/PTO			Application Number	10/625,480	١
		•		Filing Date	July 22, 2003	1
	RMATION DISC			First Named Inventor	Chen, et al.	1
STATEMENT BY APPLICANT				Group Art Unit	2818	1
				Examiner Name	Phuc T. Dang	1
(Use as many sheets as necessary)				Attorney Docket Number	AMAT/5335.Y1/CPI/COPPER/PJS	1
Sheet	5	of	9	Submission Date	April 1, 2005	ţ

				U.S. PATENT	DOCUMENTS	-
Examiner Cite Document Number				Publication Date	Name of Patentee or	Pages, Columns, Lines, Where
initials		NO.	Number-Kind Code <sup>2 (I known)</sup>	MM-DD-YYYY	Applicant of Cited Document	Relevant Passages or Relevant Figures Appear
P	D	A113	US-20030054631	3/20/2003	Raaijmakers, et al.	
1	A114 US-20030072884		4/17/2003	Zhang, et al.		
		A115	US-20030072975	4/17/2003	Shero, et al.	
	,	A116	US-20030082296	5/1/2003	Elers, et al.	
		A117	US-20030082300	5/1/2003	Todd, et al.	
	, •	A118	US-20030082301	5/1/2003	Chen, et al.	
		A119	US-20030082307	5/1/2003	Chung, et al.	<del></del>
		·A120	US-20030089308	5/15/2003	Raaijmakers, et al.	
:		A121	US-20030089942	5/15/2003	Bhattacharyya	
		A122	US-20030101927	6/5/2003	Raaljmakers	
Jehranie		"A123"	· US-20030106490··	6/12/2003	Jallepally, et al.	
		A124	US-20030108674	6/12/2003	Chung, et al.	
Franc		A125	US-20030116087	6/26/2003	Nguyen, et al.	
j. idag.		A126	US-20030116804	6/26/2003	Visokay, et al.	
• • ]		A127	US-20030124262	7/3/2003	Chen, et al.	
		A128	US-20030129826	7/10/2003	Werkhoven, et al.	<del></del>
-		A129	US-20030134508	7/17/2003	Raaijmakers, et al.	
• • •		A130	US-20030143328	7/31/2003	Chen, et al.	<del></del>
		A131	US-20030143839	7/31/2003	Raaijmakers, et al.	
		A132	US-20030143841	7/31/2003	Yang, et al.	
		.A133	US-20030160277	8/28/2003	Bhattacharyya	
		A134	US-20030165615	9/4/2003	Aaltonen, et al.	<del></del>
fpr 4		A135	US-20030166318	9/4/2003	Zheng, et al.	
		A136 .	US-20030168750	9/11/2003	Basceri, et al.	
	.:	A137	US-20030172872	9/18/2003	Thakur, et al.	
	<u></u>	A138	US-20030173586	9/18/2003	Moriwaki, et al.	
₩.		A139	US-20030185980	10/2/2003	Endo	
P	ワ	A140	US-20030186495	10/2/2003	Saanila, et al.	

Examiner PHUC T. DANG Date Considered 5/17/2005

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Substitute for form 1449A/PTO				Application Number	10/625,480
	•	•		Filing Date	July 22, 2003
INFO	RMATION DISC	CLOS	SURE	First Named Inventor	Chen, et al.
STAT	STATEMENT BY APPLICANT			Group Art Unit	2818
	•	•		Examiner Name	Phuc T. Dang
(Use as many sheets as necessary)			)	Attorney Docket Number	AMAT/5335.Y1/CPI/COPPER/PJS
· Sheet	6	of	9	Submission Date	April 1, 2005

Examiner	Cite	Document Number	Τ		<u> </u>		Pages, Columns, Lines, Whe	ora
nitials*	No.1	Number-Kind Code <sup>2 (t known)</sup>	Pu			Name of Patentee or Applicant of Cited Document	Relevant Passages or Relevant Figures Appear	
PP	. A141	US-20030186561 10/2		2/2003	Lav	v, et al.		
$\Lambda$	A142	US-20030189232	10/	9/2003	Lav	v, et al.		
. :	A143	US-20030190423	10/	9/2003	Yar	ng, et al.		
	· A144	· US-20030190497	10/	9/2003	Yar	ng, et al.		
	A145	US-20030190804	10/	9/2003	Gle	nn, et al.		
	A146	US-20030194853	10/	16/2003	Jec	n e		
	. A147	US-20030198754	10/	23/2003	Xi,	et al.		
	A148	US-20030205729	11/	6/2003	Bas	ceri, et al.		
	A149	US-20030213560	11/	20/2003	Wa	ng, et al.		
	A150	US-20030215570	11/	20/2003	Set	itter, et al.		-
********	A151	US-20030216981	11/	20/2003	Tilli	man		
	A152	US-20030232554	12/	18/2003	Blu	m, et al.		
3235	A153	US-20030235961	12/	25/2003	Metzner, et al.			
in a c	A154	US-20040009307	1/1	5/2004	Koh, et al.		<u></u>	
	A155	US-20040013803	1/2	2/2004	Chung, et al.		<u> </u>	
	A156	US-20040018304	1/2	9/2004	Chung, et al.			
	A157	US-20040018723	1/2	9/2004	Chung, et al.			
1/	A158	US-20040018747	1/1	5/2004	Vis	okay, et al.		
V	A159	US-20040033698	2/1	9/2004	Lee	, et al.		
PD	A160	US-20040043630	3/4	/2004	Vaa	arstra, et al.		
		F	DRE	IGN PATEI	NT I	DOCUMENTS	•	
xaminer	Cite	Foreign Patent Document		Publication D		Name of Patentee or	Pages, Columns, Lines,	Т
nitials*	No.¹	Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>8</sup> (if kno	own)	MM-DD-YY		Applicant of Cited Document	Where Relevant Passages or Relevant Figures Appear	
-PD	B1 ·	EP 1 167 569		1/2/2002		IPS LIMITED	*	
	B2	GB 2 355 727		5/2/2001		SAMSUNG ELECTRONICS CO., LTD		
,	В3	JP 07-300649		11/14/1995		KOBE STEEL LTD		
V	B4	JP 01-143221		6/5/1989		NEC CORP		
PD	B5	JP 02-246161		10/1/1990		FUJITSU LTD		

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STATEMENT BY APPLICANT			CANT	Group Art Unit	2818	†
				Examiner Name	Phuc T. Dang	†
(Use as many sheets as necessary)				Attorney Docket Number	AMAT/5335.Y1/CPI/COPPER/PJS	†
Sheet	7	of	9	Submission Date	April 1, 2005	ナ

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examiner nitials*			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
PD	P D 86 JP 10-308283		11/17/1998	DENSO CORP (US)		
<u> </u>	87	JP 2000-178735	6/27/2000	-		
gares s.	88	JP 2000-31387	1/28/2000	FUJI ELECTRIC CO LTD		
: .	· B9	JP 2000-58777	2/25/2000	SAMSUNG ELECTRONICS CO., LTD		
	B10	JP 2001-111000	4/20/2001			<u> </u>
	B11	JP 2001-172767	6/18/2002	ASM MICROCHEMISTRY OY	·	
	B12	'JP 2001-220294	8/14/2001	DENSO CORP		
7.7	B13	JP 2001-254181	9/18/2001	TOKYO ELECTRON LTD		
	B14	WO 00/15865	3/23/2000	ASM MICROCHEMISTRY		
(m. g. v.m.	B15	WO 00/16377	3/23/2000	GENITECH CO., LTD.	<del></del>	Г
- 1	B16	WO 00/54320	9/14/2000	GENUS, INC.		
	. B17	WO 00/63957	10/26/2000	GENITECH CO., LTD.	<del></del>	Г
negram relativ	B18	WO 00/79576	12/28/2000	GENITECH INC.		Г
	B19	WO 01/15220	3/1/2001	ASM AMERICA, INC.		
. : -	B20	WO 01/17692	3/15/2001	ASM AMERICA, INC.		<u> </u>
	B21	WO 01/27346	4/19/2001	ASM MICROCHEMISTRY OY		
	B22	WO 01/27347	4/19/2001	ASM MICROCHEMISTRY OY		
	B23	WO 01/29280	4/26/2001	ASM AMERICA, INC.		
1.	B24	WO 01/29891	4/26/2001	ASM AMERICA, INC.		Γ
	B25	WO 01/29893	4/26/2001	ASM AMERICA, INC.		Г
[.	B26	WO 01/66832	9/13/2001	ASM AMERICA, INC.		Γ
	B27	WO 02/01628	1/3/2002	APPLIED.MATERIALS, INC.		
	628	WO 02/45167	6/6/2002	ASM MICROCHEMISTRY OY		
٠	B29	WO 02/45871	6/13/2002	ANGSTRON SYSTEMS, INC.		
	B30	WO 02/67319	8/29/2002	ASM MICROCHEMISTRY OY		
V	B31	WO 96/17107	6/6/1996	MIKROKEMIA OY		
PD	B32	WO 98/51838	11/19/1998	APPLIED MATERIALS, INC.		Γ

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				Examiner Name	Phuc T. Dang	I
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,	<del>,</del>	,	FORE	IGN PATENT I	DOCUMENTS			
Examiner nitials*	Cite No. <sup>1</sup>	Co	Foreign Patent Document untry Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
PD	B33	WC	99/01595	1/14/1999 NESTE OY				
PD	B34	WC	99/29924	6/17/1999	NESTE OYJ			
			NON PATE	NT LITERATU	JRE DOCUMENTS			
Examiner Initials*	Cite.N	۱o. ۱	Include name of the author (in C/ magazine, journal, serial, sympos	ium, catalog, etc.), d			T²	
10	C1 ·	•	George, et al. "Surface Chemistry	for Atomic Layer Gr	owth," J. Phys. Chem. 1996, 100,	pp. 13121-13131		
. "	C2		Hwang, et al. "Nanometer-Size α- Metamorphism," Science Vo. 288		arnet: A Thermobarometer for Ulti	rahigh-Pressure		
	СЗ		Klaus, et al. "Atomic Layer Deposi Surface Review and Letters, Vol. (			miting Surface Reactions,"		
	C4		Lee, et al. "Cyclic Technique for th (1997) pp. 264-269	ne Enhancement of h	lighly Orlented Diamond Film Gro	owth," Thin Solid Films 303		
- in -varr uit	C5		Martensson, et al. "Use of Atomic Vol. 17, No. 5, (Sept. 1999) pp.21		brication of SVTIN/Cu Structures,	J. Vac. Sci. & Tech. B,		
	C6	-	Min, et al. "Atomic Layer Deposition Res. Soc. Symp. Proc. Vol. 514 (1		by Sequential Introduction of TI P	recursor and NH <sub>3</sub> ," Mat.		
	C7		Min, et al. "Chemical Vapor Depos Proc. Vol. 564 (1999) pp. 207-210		s with Alternating Source Supply,	Mat. Res. Soc. Symp.		
	C8		Min, et al. "Metal-organic Atomic-l. 75, No. 11 (11 Sep 1999) pp. 152		tanium-silicon-nitride Films," App	lied Physics Letters, Vol.		
	C9		Niinisto, et al. "Synthesis of Oxide Materials Science and Engineering		rlayers by Atomic Layer Epitaxy fo	or Advanced Applications,*		
	C10		Proceedings of the ICEEE 1998 In June 1-3, 1998	nternational Intercon	nect Technology Conference - Sa	an Francisco, California,		
	C11		Ritala, et al. "Atomic Force Micros Thin Solid Films, Vol. 228, No. 1-2			Atomic Layer Epitaxy,"	******	
	C12		Ritala, et al. "Atomic Layer Epitaxy No. 8 (Aug, 1998) pp. 2914-20	Growth of TiN Thin	Films From Til <sub>4</sub> and NH <sub>3</sub> ," J. Elec	trochem. Soc., Vol. 145,	•	
PO	C13		Ritala, et al. "Atomic Layer Epitaxy	y Growth of TiN Thin	Films," J. Electrochem. Soc., Vol	. 142, No. 8, August 1995		

Examiner PHUC T. DANG Date Considered 5/17/2005

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				Examiner Name	Phuc T. Dang
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Sheet	9	of	9	Submission Date	April 1, 2005

	<u> </u>	NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T²
PP	C14	Ritala, et al. "Effects of Intermediate Zinc Pulses on Properties of TiN and NbN Films by Atomic Layer Epitaxy," Applied Surface Science, Vol. 120, No. 3-4, (Dec. 1997), pp. 199-212	
<i></i>	C15	Ritala, et al. "Growth of Tilanium Dioxide Thin Films by Atomic Layer Epitaxy," Thin Solid Films, Vol. 225, No. 1-2 (25 March 1993) pp. 288-95	
	C16	Ritala, et al. "Perfectly Conformal TiN and Al <sub>2</sub> O <sub>3</sub> Films Deposited by Atomic Layer Deposition," Chem. Vap. Deposition 1999, 5, No. 1	
*/	Ç17	Ritala, et al. "Surface Roughness Reduction in Atomic Layer Epitaxy Growth of Titanium Dioxide Thin Films," Thin Solid-Films, Vol. 249, No. 2 (15 Sept. 1994), pp. 155-62	
PD	C18	Rossnagel, et al. "Plasma-enhanced Atomic Layer Deposition of Ta and Ti for Interconnect Diffusion Barriers," J. Vacuum Sci. & Tech. B., Vol. 18, No. 4 (July 2000), pp. 2016-20	
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